

Silicon Carbide (SiC) **Schottky Diode** - EliteSiC, 40 A, 1200 V, D1, TO-247-2L

FFSH40120A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

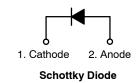
Features

- Max Junction Temperature 175°C
- Avalanche Rated 420 mJ

- No Reverse Recovery/No Forward Recovery
 This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

 Applications
 General Purpose
 SMPS, Solar Inverter, UPS
 Power Switching Circuits

 A YWW
 ZZ
 FFSH40120A





MARKING DIAGRAM



= Assembly Plant Code = Date Code (Year & Week)

= Lot Code

= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of

1

FFSH40120A

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage		1200	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		420	mJ
I _F	Continuous Rectified Forward Current @ T _C < 155°C		40	Α
	Continuous Rectified Forward Current @ T _C < 135°C		61	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1650	Α
		T _C = 150°C, 10 μs	1550	Α
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	270	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	120	Α
Ptot	Power Dissipation	T _C = 25°C	682	W
		T _C = 150°C	114	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	M °C
	TO247 Mounting Torque, M3 Screw		60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 420 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 41 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	\$0,	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	CO, a	0.22	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	$I_F = 40 \text{ A}, T_C = 25^{\circ}\text{C}$	0R-11	1.45	1.75	V
		I _F = 40 A, T _C = 125°C	0,-	1.7	2.0	
		$I_F = 40 \text{ A}, T_C = 175^{\circ}\text{C}$	ı	2.0	2.4	
I _R	Reverse Current	$V_R = 1200 \text{ V, } T_C = 25^{\circ}\text{C}$	ı	-	200	μΑ
	CEPLE	V _R = 1200 V, T _C = 125°C	ı	ı	300	
		V _R = 1200 V, T _C = 175°C	ı	ı	400	
Q_C	Total Capacitive Charge	V = 800 V	ı	220	_	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	_	2250	_	pF
11		V _R = 400 V, f = 100 kHz	_	204	_]
*		V _R = 800 V, f = 100 kHz	-	169	=	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH40120A	FFSH40120A	TO-247-2LD (Pb-Free/Halogen Free)	30 Units / Tube

FFSH40120A

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

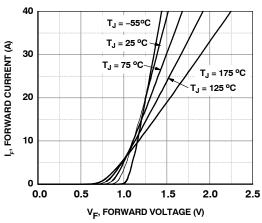


Figure 1. Forward Characteristics

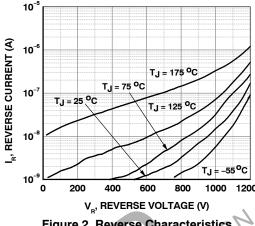


Figure 2. Reverse Characteristics

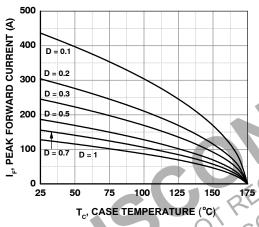


Figure 3. Current Derating

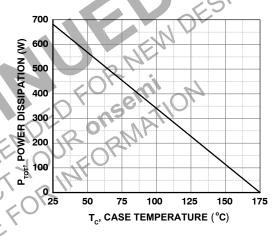


Figure 4. Power Derating

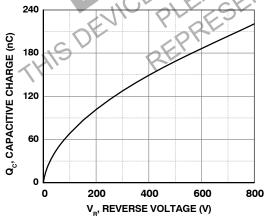


Figure 5. Capacitive Charge vs. Reverse Voltage

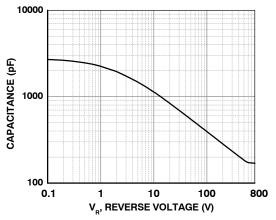


Figure 6. Capacitance vs. Reverse Voltage

FFSH40120A

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

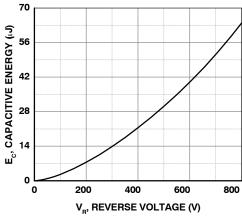


Figure 7. Capacitance Stored Energy

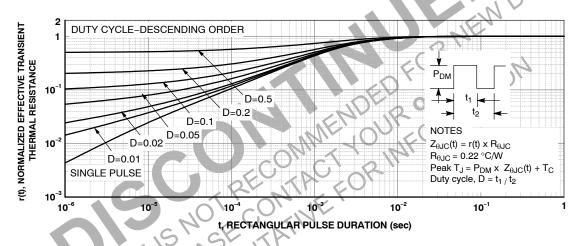
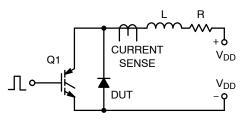


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$$\begin{split} L &= 0.5 \text{ mH} \\ R &< 0.1 \text{ }\Omega \\ V_{DD} &= 50 \text{ }V \\ \text{EAVL} &= 1/2 \text{L12} \left[V_{R(AVL)} / \left(V_{R(AVL)} - V_{DD} \right) \right] \\ Q1 &= \text{IGBT} \left(BV_{CES} > \text{DUT} \ V_{R(AVL)} \right) \end{split}$$



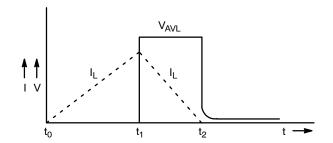
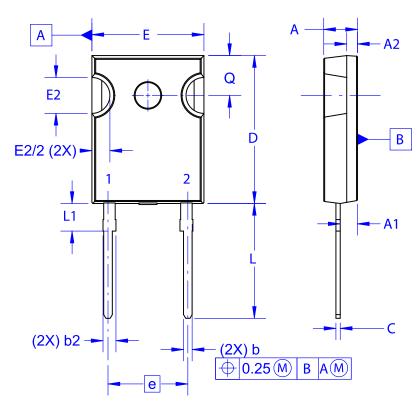


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

DATE 03 DEC 2019



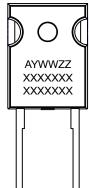






- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
 D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

= Assembly Location

= Year

= Work Week WW

= Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

Ø P —		Ø P1 D2
S E1 —		D1
		J

DIM	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A1	2.29	2.40	2.66	
A2	1.30	1.50	1.70	
b	1.17	1.26	1.35	
b2	1.53	1.65	1.77	
С	0.51	0.61	0.71	
D	20.32	20.57	20.82	
D1	16.37	16.57	16.77	
D2	0.51	0.93	1.35	
Е	15.37	15.62	15.87	
E1	12.81	~	~	
E2	4.96	5.08	5.20	
е	~	11.12	~	
L	15.75	16.00	16.25	
L1	3.69	3.81	3.93	
ØΡ	3.51	3.58	3.65	
Ø P 1	6.61	6.73	6.85	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	

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DESCRIPTION:	TO-247-2LD		PAGE 1 OF 1	

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